

#### **EMI Reduction IC**

#### **Features**

- FCC approved method of EMI attenuation.
- Provides up to 15dB EMI reduction.
- Generates a 1X low EMI spread spectrum clock of the input frequency.
- Input frequency range: 6MHz to 90MHz.
- Internal loop filter minimizes external components and board space.
- Selectable spread options: Down and Center Spread
- 2 spread frequency deviation selections:
  - -1.25% or ± 0.42%
- Low inherent cycle-to-cycle jitter.
- Supply Voltage: 3.3 V ± 0.3V.
- Low power CMOS design.
- Supports notebook VGA and other LCD timing controller applications.
- Products are available for Industrial temperature range.
- Available in 8-pin SOIC and TSSOP Packages.

#### **Product Description**

The ASM3P2183A is a versatile spread spectrum frequency modulators designed specifically for a wide range of input clock frequencies from 6MHz to 90MHz. (Refer Input Frequency and Modulation Rate Table). The ASM3P2183A can generate an EMI reduced clock from an OSC or a system generated clock. The ASM3P2183A offers a Down Spread clock with a percentage deviation of -1.25% and a Center Spread clock with a percentage deviation of ± 0.42%.

The ASM3P2183A reduces electromagnetic interference (EMI) at the clock source, allowing system wide reduction of EMI of down stream clock and data dependent signals. The ASM3P2183A allows significant system cost savings by reducing the number of circuit board layers ferrite beads, shielding and other passive components that are traditionally required to pass EMI regulations.

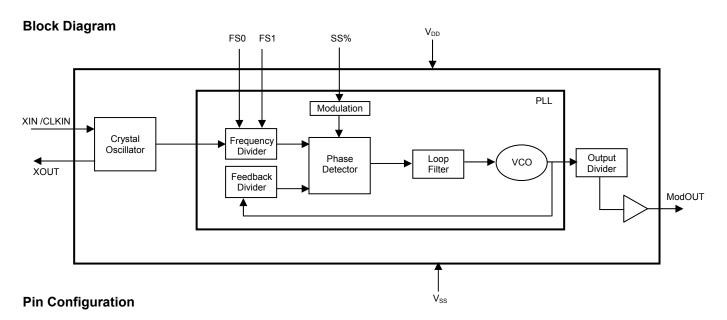
The ASM3P2183A uses the most efficient and optimized modulation profile approved by the FCC and is implemented in a proprietary all digital method.

The ASM3P2183A modulates the output of a single PLL in order to "spread" the bandwidth of a synthesized clock, and more importantly, decreases the peak amplitudes of its harmonics. This results in significantly lower system EMI compared to the typical narrow band signal produced by oscillators and most frequency generators. Lowering EMI by increasing a signal's bandwidth is called 'spread spectrum clock generation'.

#### **Applications**

The ASM3P2183A is targeted towards EMI management for memory and LVDS interfaces in mobile graphic chipsets and high-speed digital applications such as PC peripheral devices, consumer electronics, and embedded controller systems.





## 

SS%

## **Pin Description**

Pin#	Pin Name	Туре	Description
1	XIN /CLKIN	I	Crystal connection or external frequency input. This pin has dual functions. It can be connected to either an external crystal or an external reference clock.
2	XOUT	I	Crystal connection. Input connection for an external crystal. If using an external reference, this pin must be left unconnected.
3	V <sub>SS</sub>	Р	Ground to entire chip.
4	SS%	I	Spread range select. Digital logic input used to select frequency deviation (Refer <i>Spread Deviation Selection Table</i> ). This pin has an internal pull-up resistor.
5	ModOUT	0	Spread spectrum low EMI output.
6	$V_{DD}$	Р	Power supply for the entire chip.
7	FS0	I	Frequency range select. Digital logic input used to select frequency range (Refer Input Frequency and Modulation Rate Table). This pin has an internal pull-up resistor.
8	FS1	ı	Frequency range select. Digital logic input used to select frequency range (Refer Input Frequency and Modulation Rate Table). This pin has an internal pull-up resistor.

5 ModOUT



### **Input Frequency and Modulation Rate Table**

FS1 (pin 8)	FS0 (pin 7)	Frequency Range
0	0	6MHz to 13MHz
0 1		12MHz to 25MHz
1	0	25MHz to 50MHz
1	1	50MHz to 90MHz

### **Spread Deviation Selection Table**

SS% (pin 4)	Spread Deviation (%)
0	- 1.25
1	± 0.42

## **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Unit
$V_{DD},V_{IN}$	Voltage on any pin with respect to Ground	-0.5 to +4.6	V
T <sub>STG</sub>	Storage temperature	-65 to +125	°C
Ts	Max. Soldering Temperature (10 sec)	260	°C
TJ	Junction Temperature	150	°C
T <sub>DV</sub>	Static Discharge Voltage (As per JEDEC STD22- A114-B)	2	KV

Note: These are stress ratings only and are not implied for functional use. Exposure to absolute maximum ratings for prolonged periods of time may affect device reliability.

### **Recommended Operating Conditions**

Symbol	Parameter	Min	Тур	Max	Units
T <sub>A</sub>	Operating Temperature	0		+70	°C
VDD	Core Voltage	+3.0	+3.3	+3.6	V

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### **DC Electrical Characteristics**

Symbol	Parameter	Min	Тур	Max	Unit
V <sub>IL</sub>	Input low voltage	V <sub>SS</sub> – 0.3	-	0.8	V
$V_{IH}$	Input high voltage	2.0	-	V <sub>DD</sub> + 0.3	V
I <sub>IL</sub>	Input low current	-	-	-35	μΑ
I <sub>IH</sub>	Input high current	-	-	35	μΑ
I <sub>XOL</sub>	XOUT Output low current (@ 0.4V, $V_{DD} = 3.3V$ )	-	3	-	mA
I <sub>XOH</sub>	XOUT Output high current (@ 2.5V, $V_{DD} = 3.3V$ )	-	3	-	mA
$V_{OL}$	Output low voltage ( $V_{DD} = 3.3V$ , $I_{OL} = 20mA$ )	-	-	0.4	V
$V_{OH}$	Output high voltage ( $V_{DD} = 3.3V$ , $I_{OH} = 20mA$ )	2.5	-	-	V
I <sub>CC</sub>	Dynamic supply current Normal mode (3.3V,90MHz and 10pF loading)	-	28	-	mA
I <sub>DD</sub>	Static supply current *	-	7.0	-	mA
$V_{DD}$	Operating voltage	3.0	3.3	3.6	V
t <sub>ON</sub>	Power up time (first locked clock cycle after power up)	-	0.18	-	mS
Z <sub>OUT</sub>	Clock out impedance	-	50	-	Ω
* XIN /CLKIN	pin is pulled low				

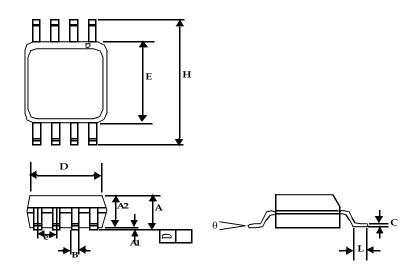
## **AC Electrical Characteristics**

Symbol	Parameter		Тур	Max	Unit		
f <sub>IN</sub>	Input frequency	6	-	90	MHz		
ModOUT	Output frequency	6	-	90	MHz		
t <sub>LH</sub> *	Output rise time (measured at 0.8V to 2.0V)	0.3	0.9	1.1	nS		
t <sub>HL</sub> *	Output fall time (measured at 2.0V to 0.8V)	0.5	1.0	1.2	nS		
t <sub>JC</sub>	Jitter (cycle to cycle)		-	200	pS		
T <sub>D</sub>	Output duty cycle	45	50	55	%		
* t <sub>LH</sub> and t <sub>HL</sub> are measured with a capacit	* t <sub>LH</sub> and t <sub>HL</sub> are measured with a capacitive load of 15pF at 27MHz						



## **Package Information**

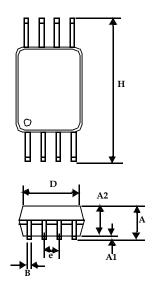
# 8-lead (150-mil) SOIC Package

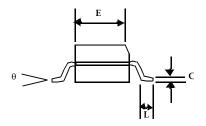


	Dimensions				
Symbol	Inches		Millimeters		
	Min	Max	Min	Max	
A1	0.004	0.010	0.10	0.25	
Α	0.053	0.069	1.35	1.75	
A2	0.049	0.059	1.25	1.50	
В	0.012	0.020	0.31	0.51	
С	0.007	0.010	0.18	0.25	
D	0.193	BSC	4.90	BSC	
Е	0.154 BSC		3.91 BSC		
е	0.050	0.050 BSC 1.27 BSC		BSC	
Н	0.236 BSC		6.00 BSC		
L	0.016	0.050	0.41	1.27	
θ			8°		



# 8-lead Thin Shrunk Small Outline Package (4.40-MM Body)





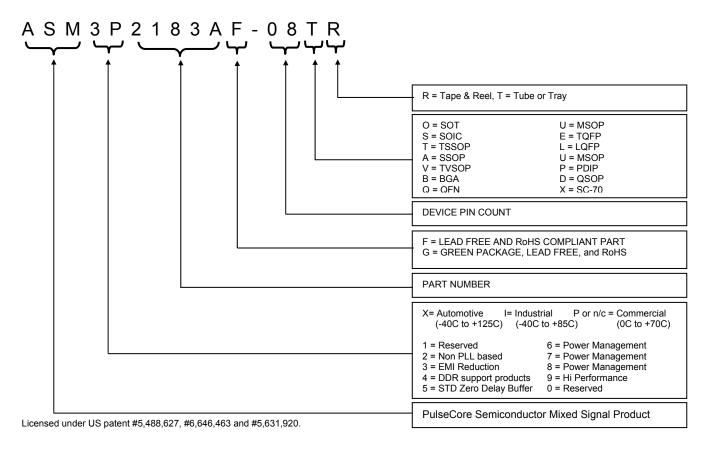
	Dimensions				
Symbol	Inc	hes	Millimeters		
	Min	Max	Min	Max	
Α		0.043		1.10	
A1	0.002	0.006	0.05	0.15	
A2	0.033	0.037	0.85	0.95	
В	0.008	0.012	0.19	0.30	
С	0.004	0.008	0.09	0.20	
D	0.114	0.122	2.90	3.10	
Е	0.169	0.177	4.30	4.50	
е	0.026	BSC	0.65 BSC		
Н	0.252 BSC		6.40	BSC	
L	0.020	0.028	0.50	0.70	
θ	0°	8°	0°	8°	



### **Ordering Information**

Part Number	Marking	Package Type	Temperature
ASM3P2183A-08ST	3P2183A	8-Pin SOIC, TUBE	Commercial
ASM3P2183A-08SR	3P2183A	8-Pin SOIC, TAPE & REEL	Commercial
ASM3P2183A-08TT	3P2183A	8-Pin TSSOP, TUBE	Commercial
ASM3P2183A-08TR	3P2183A	8-Pin TSSOP, TAPE & REEL	Commercial
ASM3P2183AF-08ST	3P2183AF	8-Pin SOIC, TUBE, Pb Free	Commercial
ASM3P2183AF-08SR	3P2183AF	8-Pin SOIC, TAPE & REEL, Pb Free	Commercial
ASM3P2183AF-08TT	3P2183AF	8-Pin TSSOP, TUBE, Pb Free	Commercial
ASM3P2183AF-08TR	3P2183AF	8-Pin TSSOP, TAPE & REEL, Pb Free	Commercial
ASM3P2183AG-08ST	3P2183AG	8-Pin SOIC, TUBE, Green	Commercial
ASM3P2183AG-08SR	3P2183AG	8-Pin SOIC, TAPE & REEL, Green	Commercial
ASM3P2183AG-08TT	3P2183AG	8-Pin TSSOP, TUBE, Green	Commercial
ASM3P2183AG-08TR	3P2183AG	8-Pin TSSOP, TAPE & REEL, Green	Commercial

#### **Device Ordering Information**





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Note: This product utilizes US Patent # 6,646,463 Impedance Emulator Patent issued to PulseCore Semiconductor, dated 11-11-2003

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